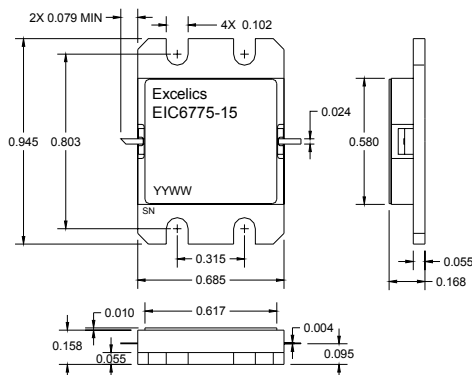


FEATURES

- 6.70– 7.50GHz Bandwidth
- Input/Output Impedance Matched to 50 Ohms
- +42.0 dBm Output Power at 1dB Compression
- 7.5 dB Power Gain at 1dB Compression
- 31% Power Added Efficiency
- 100% Tested for DC, RF, and R_{TH}



Caution! ESD sensitive device.

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

SYMBOL	PARAMETERS/TEST CONDITIONS ¹	MIN	TYP	MAX	UNITS
P_{1dB}	Output Power at 1dB Compression $f = 6.70\text{-}7.50\text{GHz}$ $V_{DS} = 10\text{ V}, I_{DSQ} \approx 4500\text{mA}$	41.0	42.0		dBm
G_{1dB}	Gain at 1dB Compression $f = 6.70\text{-}7.50\text{GHz}$ $V_{DS} = 10\text{ V}, I_{DSQ} \approx 4500\text{mA}$	7.0	8.0		dB
ΔG	Gain Flatness $f = 6.70\text{-}7.50\text{GHz}$ $V_{DS} = 10\text{ V}, I_{DSQ} \approx 4500\text{mA}$			± 0.6	dB
PAE	Power Added Efficiency at 1dB Compression $V_{DS} = 10\text{ V}, I_{DSQ} \approx 4500\text{mA}$ $f = 6.70\text{-}7.50\text{GHz}$		31		%
I_{d1dB}	Drain Current at 1dB Compression $f = 6.70\text{-}7.50\text{GHz}$		4600	5200	mA
I_{DSS}	Saturated Drain Current $V_{DS} = 3\text{ V}, V_{GS} = 0\text{ V}$		8500	11000	mA
V_P	Pinch-off Voltage $V_{DS} = 3\text{ V}, I_{DS} = 85\text{ mA}$		-2.5	-4.0	V
R_{TH}	Thermal Resistance ²		2.0	2.5	$^\circ\text{C}/\text{W}$

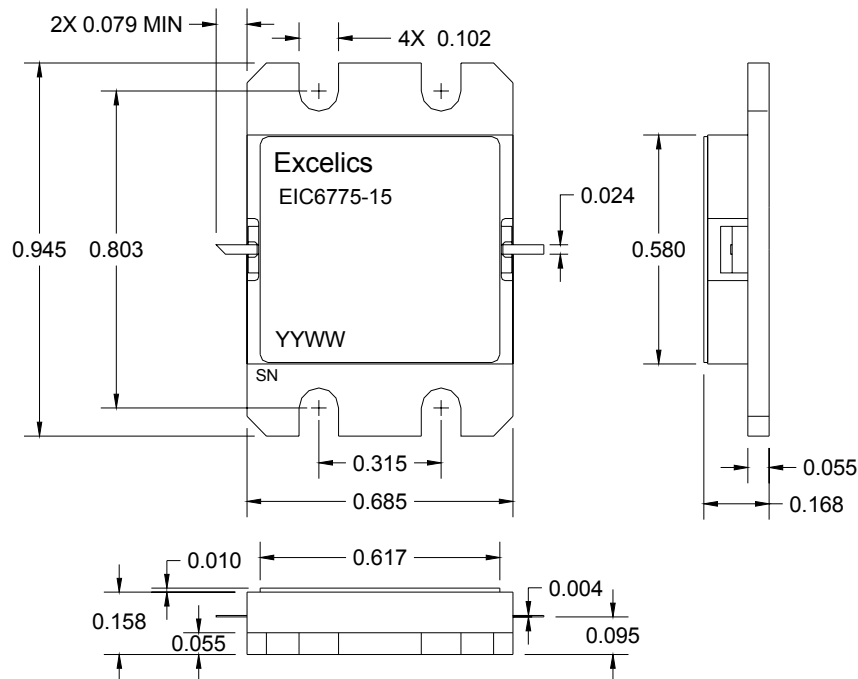
Note: 1. Tested with 50 Ohm gate resistor.
2. Overall R_{th} depends on case mounting.

ABSOLUTE MAXIMUM RATING^{1,2}

SYMBOLS	PARAMETERS	ABSOLUTE ¹	CONTINUOUS ²
V_{ds}	Drain-Source Voltage	15	10V
V_{gs}	Gate-Source Voltage	-5	-3V
I_{gsf}	Forward Gate Current	189.9mA	63.3mA
I_{gsr}	Reverse Gate Current	-10.6mA	-31.7mA
P_{in}	Input Power	41.5dBm	@ 3dB Compression
T_{ch}	Channel Temperature	175 $^\circ\text{C}$	175 $^\circ\text{C}$
T_{stg}	Storage Temperature	-65 to +175 $^\circ\text{C}$	-65 to +175 $^\circ\text{C}$
P_t	Total Power Dissipation	60W	60W

Note: 1. Exceeding any of the above ratings may result in permanent damage.
2. Exceeding any of the above ratings may reduce MTTF below design goals.

PACKAGES OUTLINE (Hermetic)



Note: Dimensions in inches, Tolerance $\pm .005$ unless otherwise specified

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness

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